

Pyroelectric Response in $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ Thin Films

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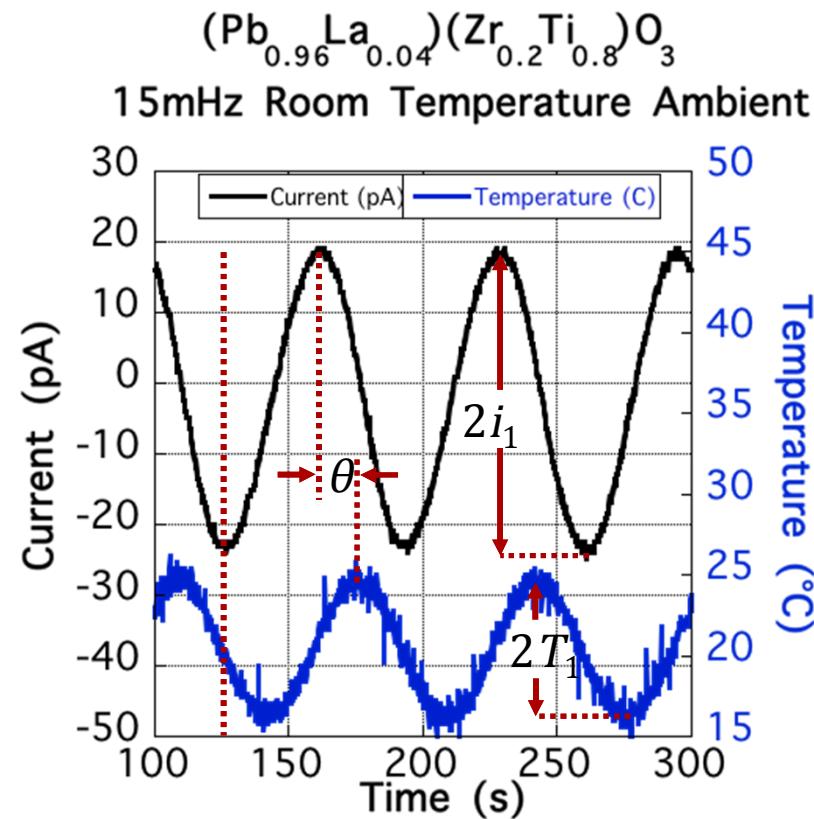
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Doped HfO₂ Pyroelectric Response

- Ferroelectric with permanent polarization must have a pyroelectric response
- Park *et al.* Nano Energy 2014
 - Hf_{1-X}Zr_XO₂ (0.7 ≤ X ≤ 0.9)
 - Measured Polarization-Electric field hysteresis curves at various Temperatures
- Hoffman *et al.* Nano Energy 2015
 - Si:HfO₂
 - Measured pyroelectric coefficient due to orthorhombic to tetragonal phase change
 - Pyroelectric current measured while sample temperature increased
- These methods can be influenced by extrinsic artifacts such as leakage current.

Pyroelectric Measurements

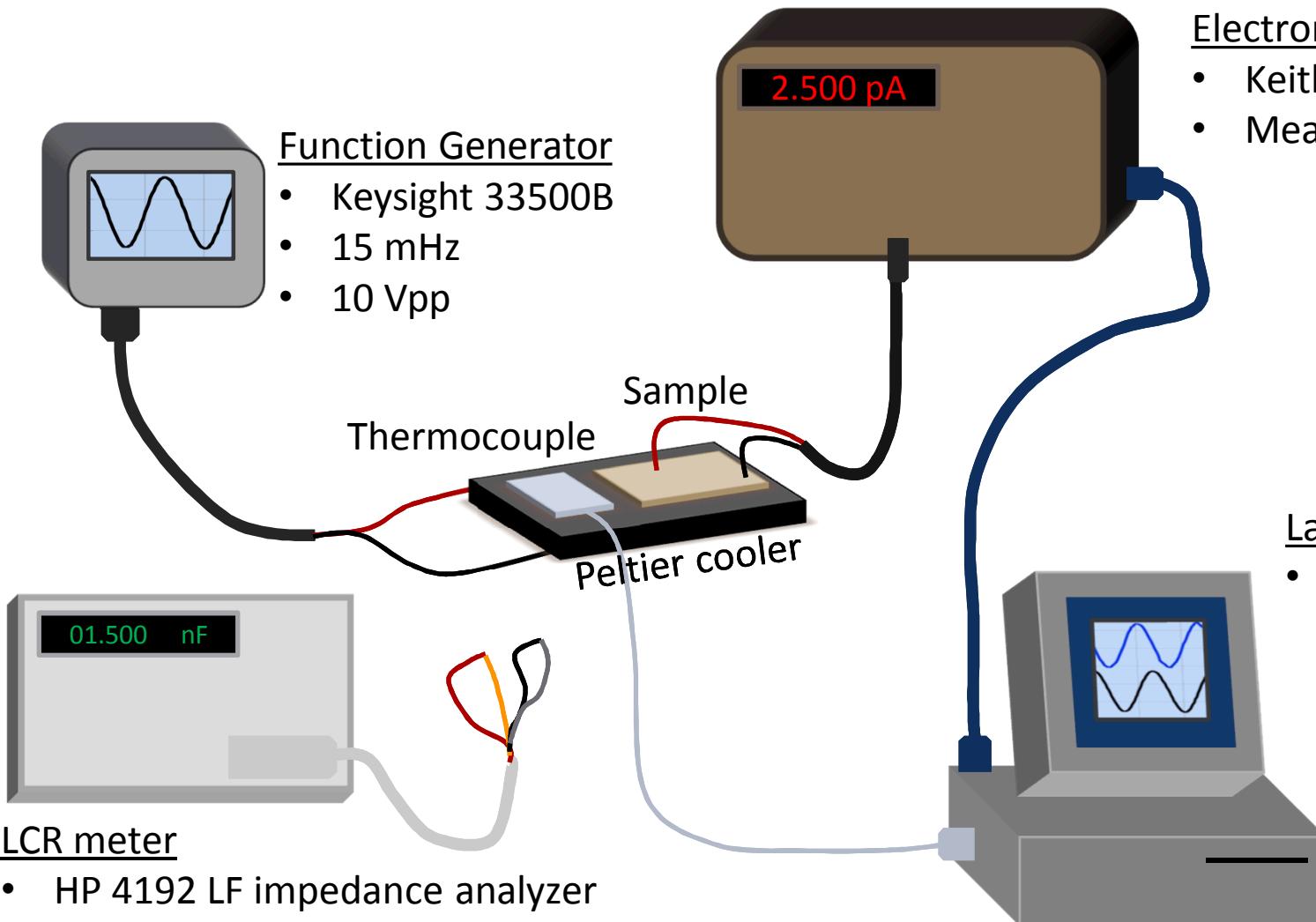
- Static
 - Charge compensation by leakage current
- Indirect
 - Incomplete switching or fatigue
- Dynamic
 - Linear temperature – (Byer-Roundy)
 - Difficult to separate pyroelectric and other thermally induced currents
 - Oscillating temperature
 - Peltier device small sinusoidal temperature waveform
 - Pyroelectric current is 90° out of phase with temperature waveform



$$i_1 \sin(\theta) = pA\omega T_1$$

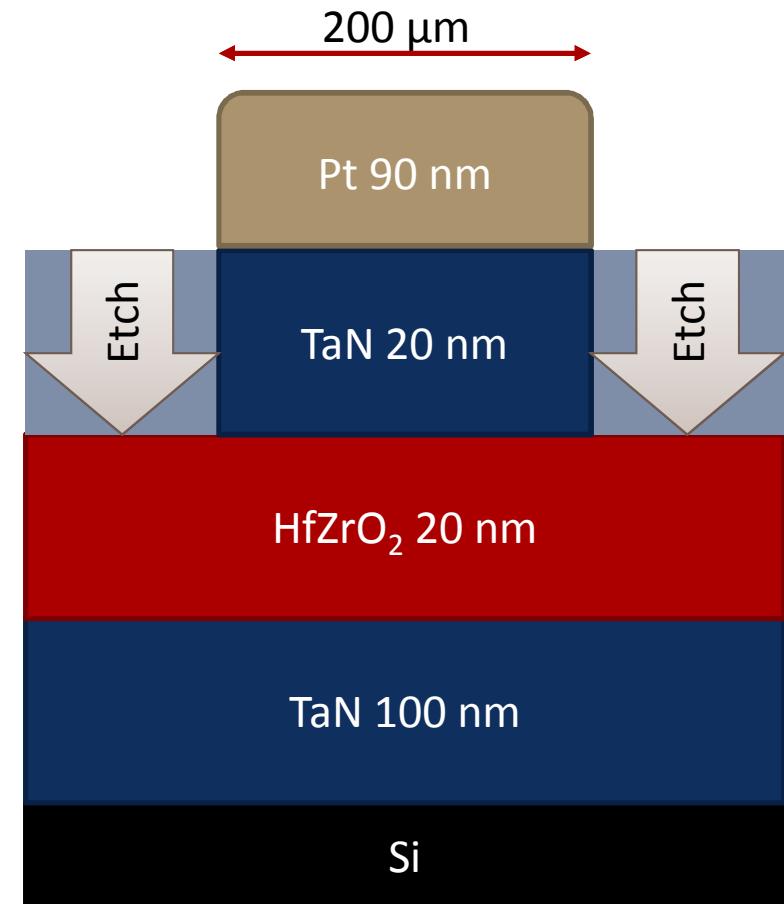
p – pyroelectric coefficient
 ω – angular frequency of temperature
 A – area of device

Pyroelectric Setup

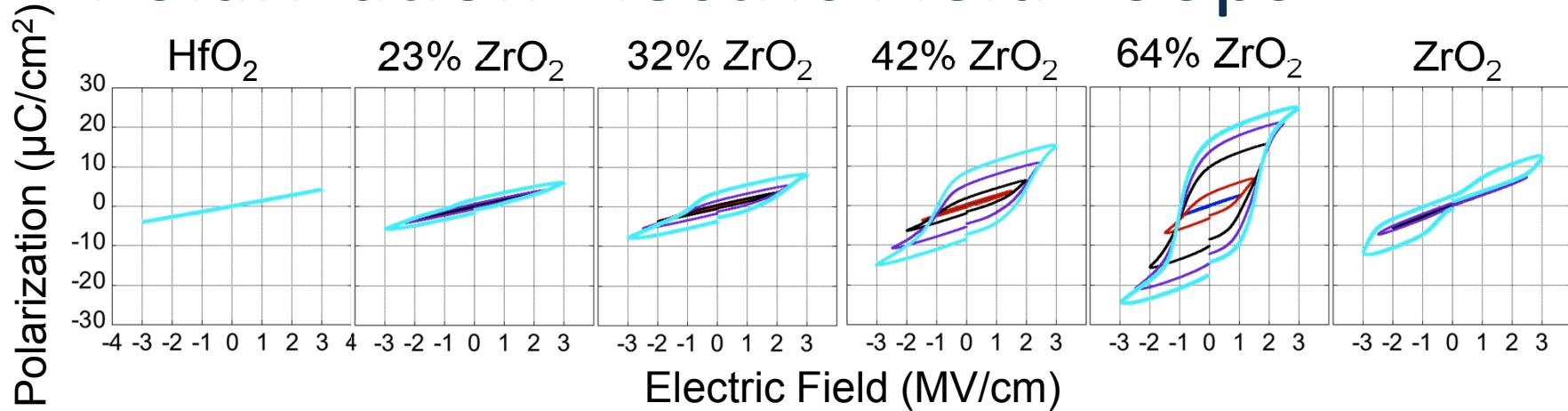


Experimental and Device Stack

- RF sputter TaN from TaN target
- Thermal ALD $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ at 150 °C by TDMA Hf, TDMA Zr, and H_2O
 - Cycle ratio to control composition
- RF sputter blanket TaN cap
- Rapid thermal anneal 30s at 600 °C under nitrogen
- Sputter Pt through shadow-mask
- ICP reactive ion etch
 - SF_6 and C_4F_8 atmosphere

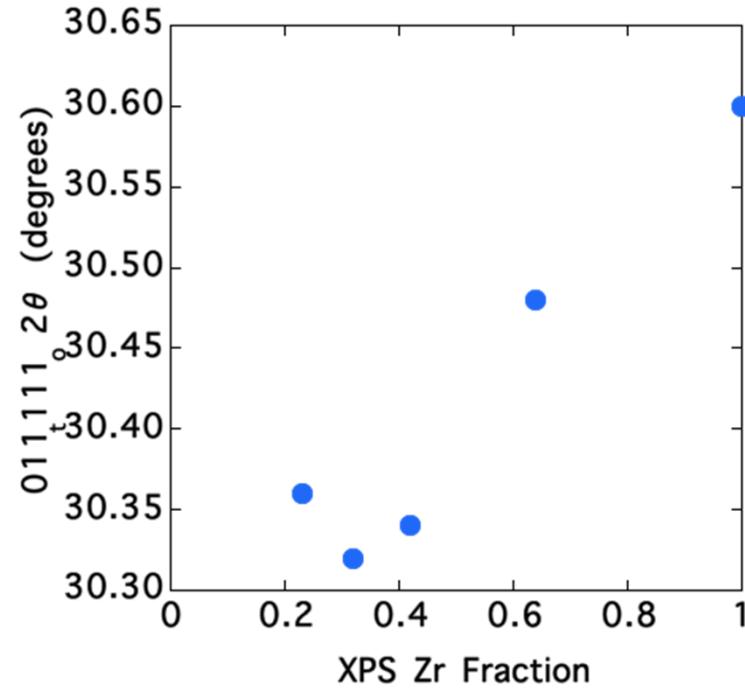
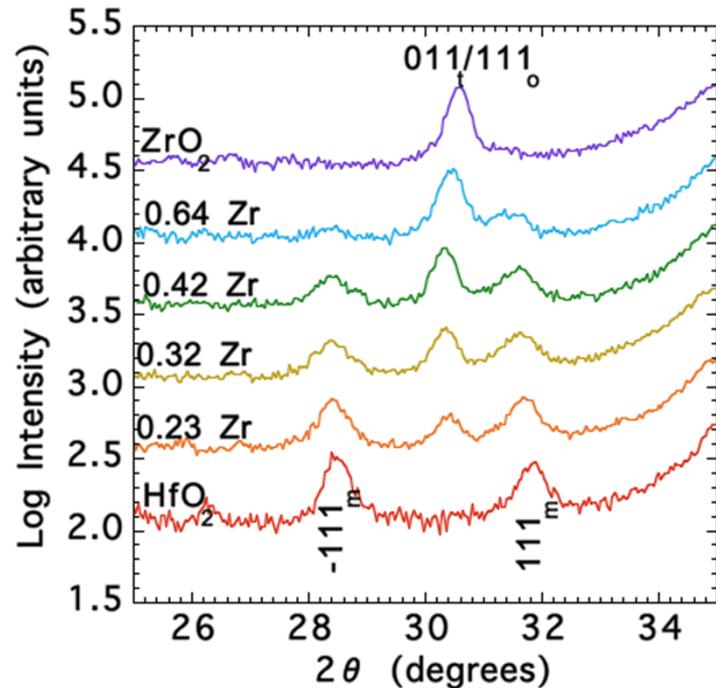


Polarization Electric Field Loops



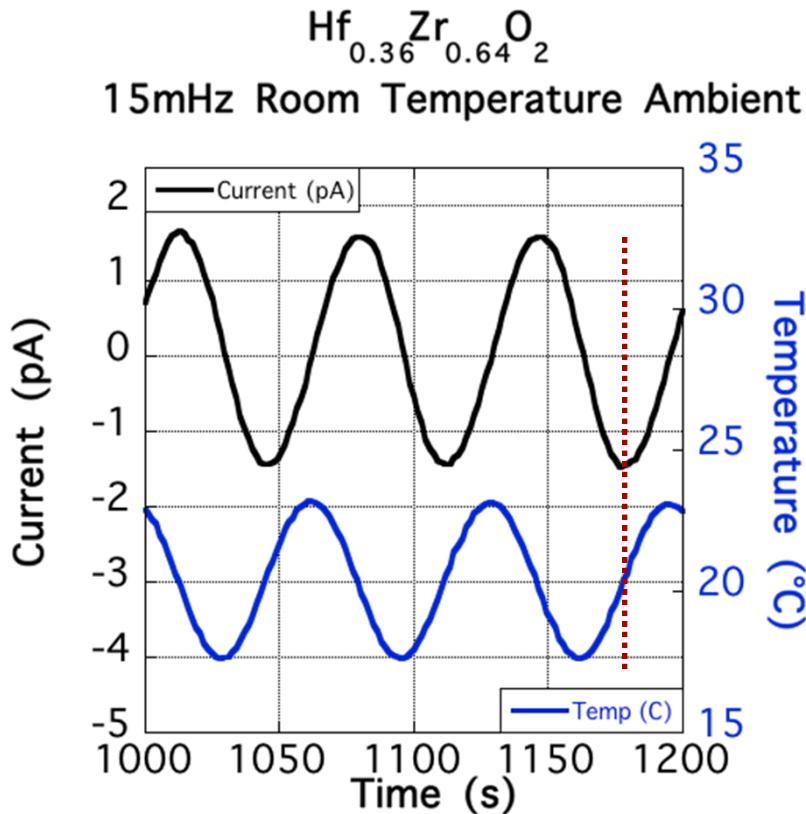
- Composition, measured by XPS, is HfO_2 rich as expected with larger HfO_2 growth per cycle.
- Trend similar to literature.
 - Antiferroelectric consistent with ZrO_2
- Remanent polarization does not saturate due to leakage current

Phase Assemblage

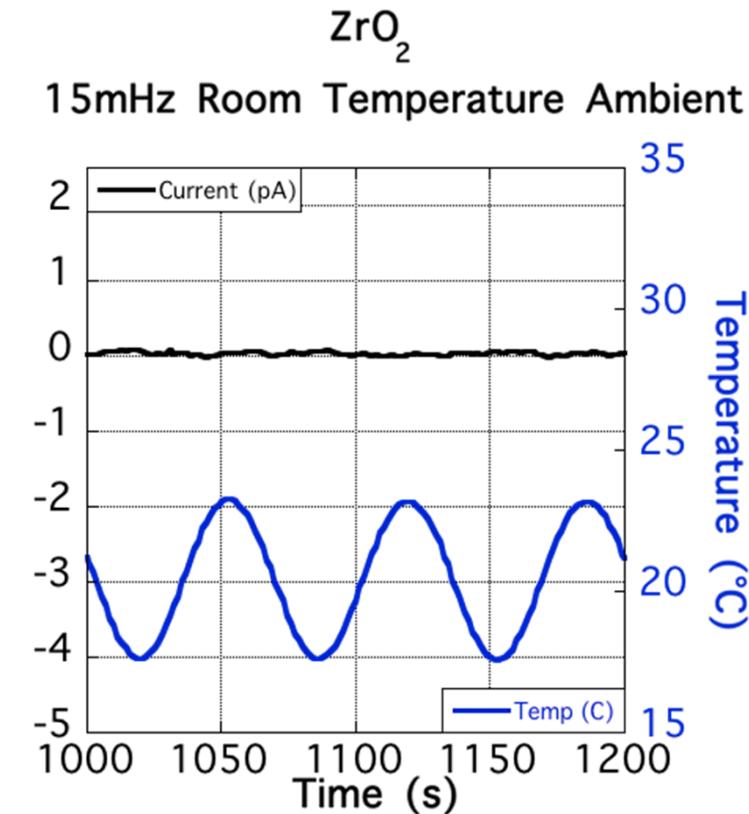


- Monoclinic peaks decrease and Orthorhombic/Tetragonal increase with increased Zr content
- 011t/111o peak shifts to higher angles with increased Zr content
- Orthorhombic/tetragonal intensity correlates with polarization response

Pyroelectric Waveforms

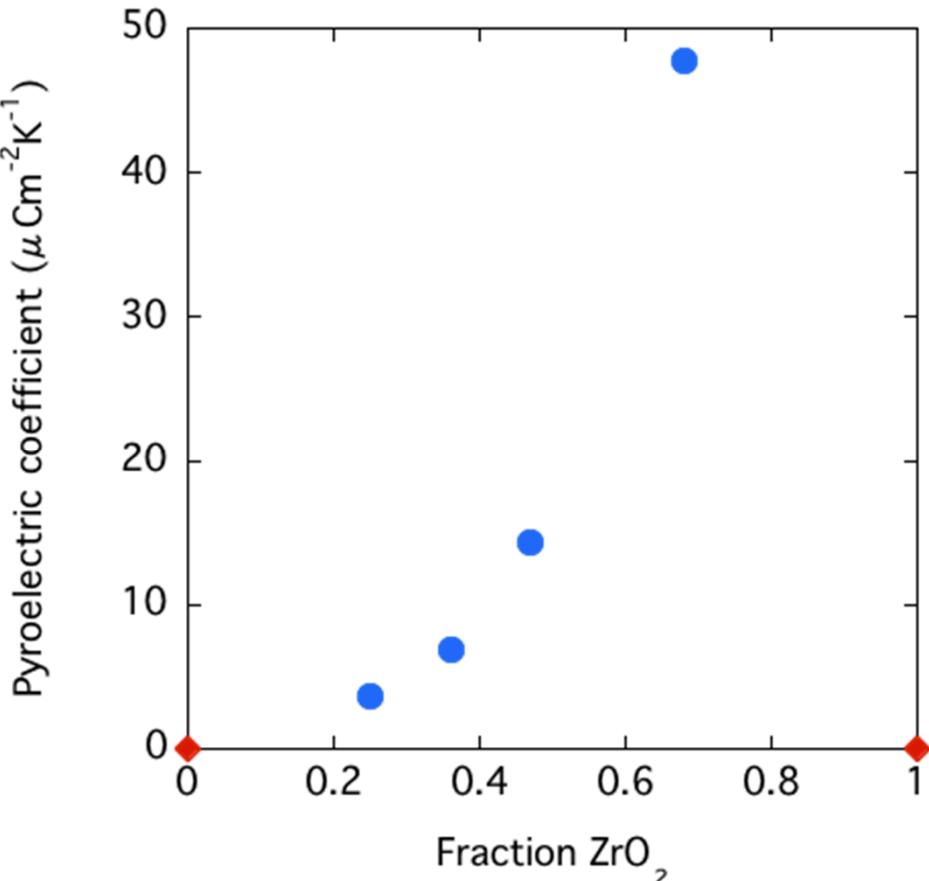


Pyroelectric current measurement for
 $\text{Hf}_{0.36}\text{Zr}_{0.64}\text{O}_2$ film.



Pyroelectric current measurement for
 ZrO_2 film.

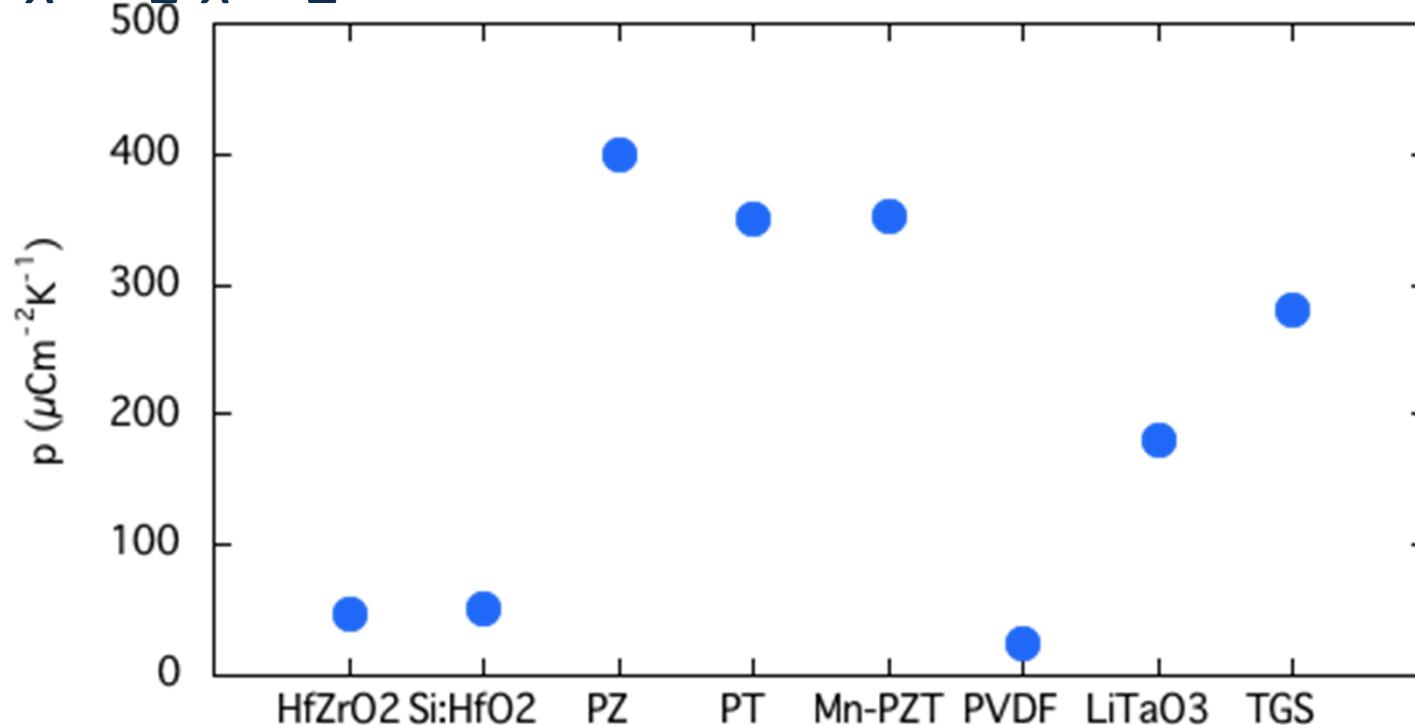
Pyroelectric Coefficients



Room temperature pyroelectric coefficient for $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ films as a function of Zr content.

- Pure HfO_2 and ZrO_2 : no pyroelectric response
- Increasing pyroelectric coefficient with Zr content
 - Maximum: $48 \mu\text{Cm}^{-2}\text{K}^{-1}$ at 68% ZrO_2
- Follows polarization and orthorhombic phase content trend.

$Hf_xZr_{1-x}O_2$ & Other Materials



| Material | p ($\mu\text{Cm}^{-2}\text{K}^{-1}$) | Dielectric properties | | $F_I 10^{-10}$ (mV^{-1}) | F_V (m^2C^{-1}) | $F_D 10^{-6}$ ($\text{Pa}^{-1/2}$) | Reference |
|------------------------------------------------------|------------------------------------------|-----------------------|---------------|-------------------------------------|-------------------------------------|--------------------------------------|---------------------------|
| | | e | $\tan \delta$ | | | | |
| Hf _{0.32} Zr _{0.68} O ₂ | 48 | 25 | 0.014 | 0.22 | 0.10* | 13* | This work |
| 5.6 mol% Si:HfO ₂ | 52 | 38 | 0.025 | 0.20 | 0.06 | 7 | Hoffmann 2015 Nano Energy |
| Mod. PZT | 400 | 290 | 0.003 | 0.02 | 0.06 | 58 | Whatmore 2004 J |
| Mod. PT | 350 | 220 | 0.01 | 0.01 | 0.07 | 32 | Electroceramics |
| Mn -PZT thin film | 352 | 257 | 0.007 | - | - | 39 | Sebald 2008 IEEE Trans. |
| PVDF | 25 | 9 | 0.03 | 0.11 | 0.14 | 7 | Ploss 1991 Sensors and |
| LiTaO ₃ | 180 | 47 | 0.005 | 0.56 | 0.14 | 39 | Actuators A |
| TGS | 280 | 38 | 0.01 | 1.2 | 0.36 | 66 | |

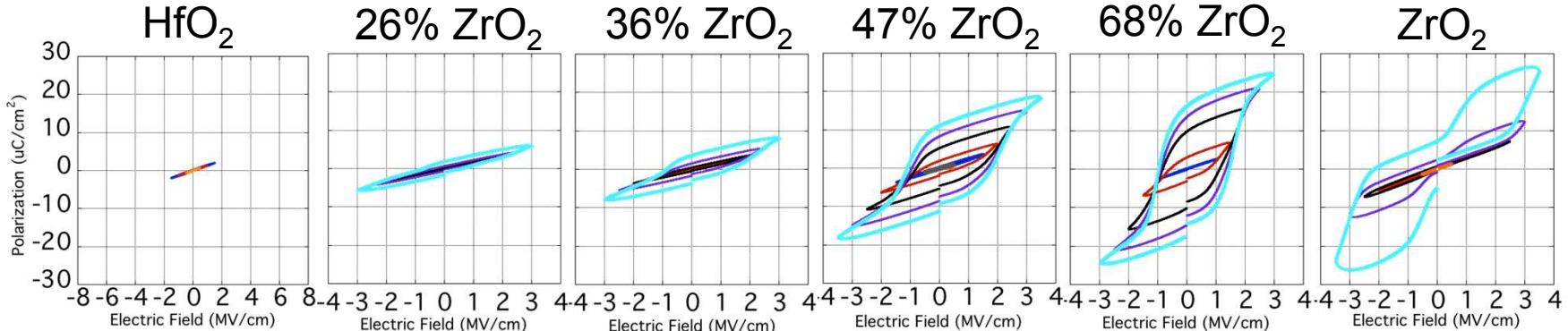
* Literature value bulk heat capacity

Conclusions

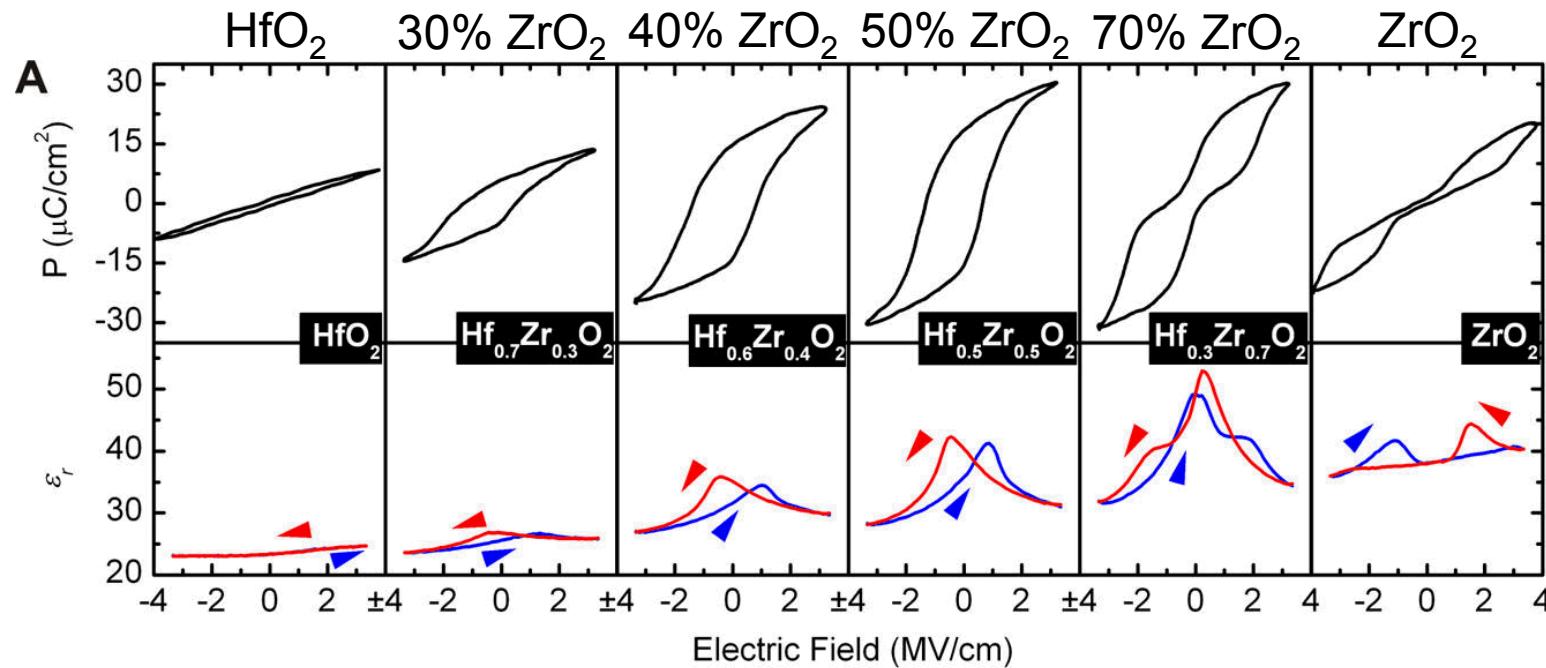
- We do observe a pyroelectric response in $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$
 - Consistent with permanent polarization
 - Consistent with ferroelectricity
- Pyroelectric response, polarization magnitude, orthorhombic/tetragonal phase fraction, are all correlated with Zr content.
- $\text{Hf}_{0.32}\text{Zr}_{0.68}\text{O}_2$ pyroelectric coefficient and IR detector figures of merit similar to PVDF and LiTaO_3
 - $p=48 \text{ } \mu\text{Cm}^{-2}\text{K}^{-1}$
 - $F_I= 0.22 \text{ mV}^{-1}$
 - $F_V= 0.10 \text{ m}^2\text{C}^{-1}$
- This could be a promising material for large area IR detectors or low frequency detection.

BONUS SLIDES

Polarization electric field loops

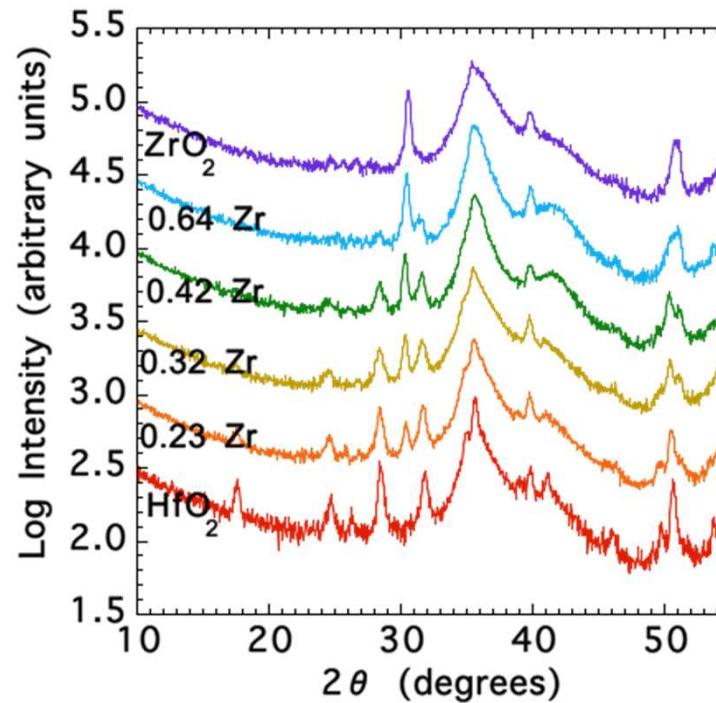
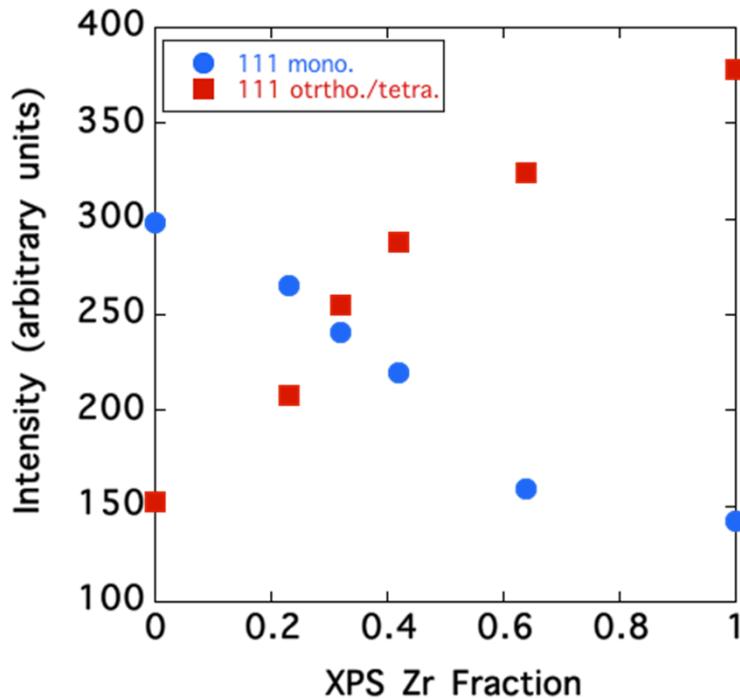


This work – 20 nm HfZrO₂ with TaN electrodes.

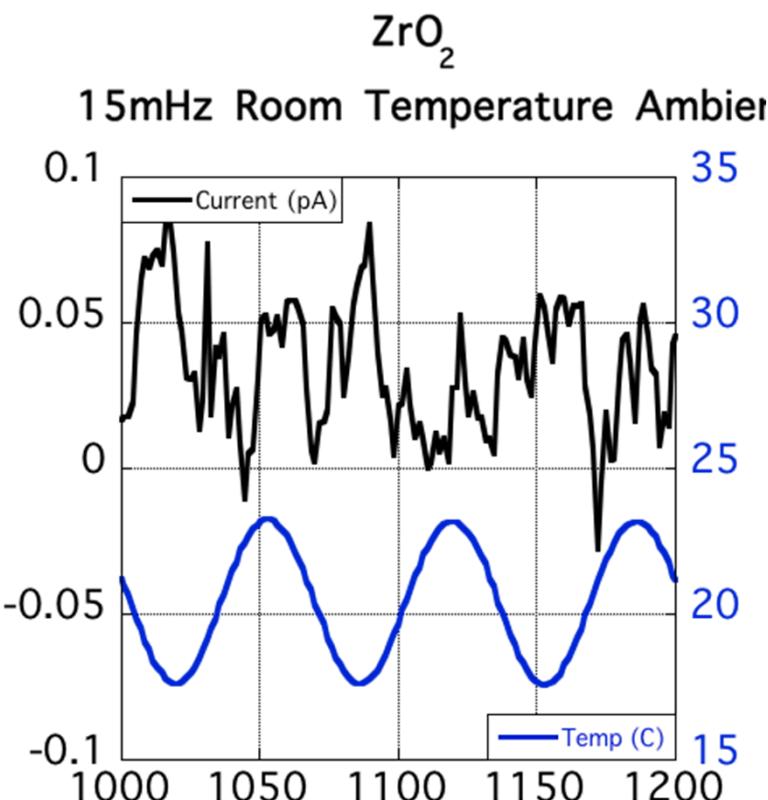


Muller 2012 Nanoletter – 9 nm HfZrO₂ with TiN electrodes.

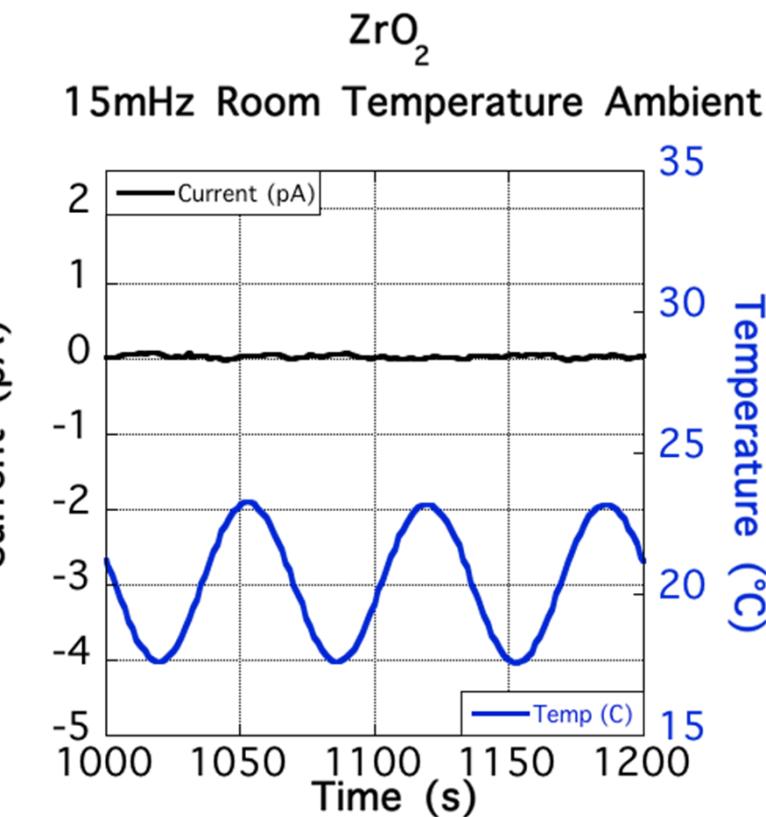
X-ray results



ZrO_2 pyro waveforms zoomed in



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